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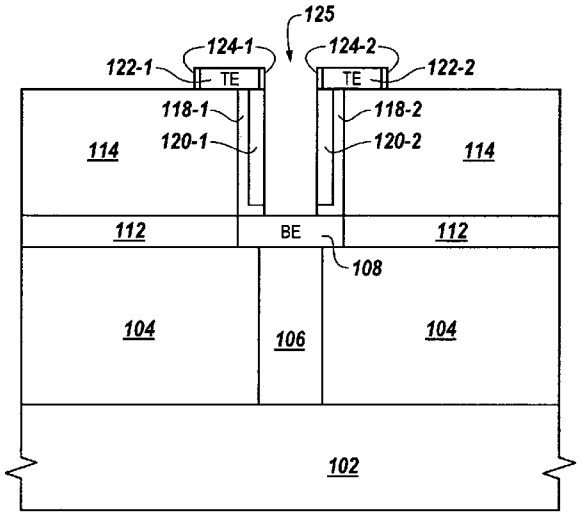


Fig. 1G

(57) Abstract: Resistance variable memory cell structures and methods are described herein. One or more resistance variable memory cell structures include a first electrode common to a first and a second resistance variable memory cell, a first vertically oriented resistance variable material having an arcuate top surface in contact with a second electrode and a non-arcuate bottom surface in contact with the first electrode; and a second vertically oriented resistance variable material having an arcuate top surface in contact with a third electrode and a non-arcuate bottom surface in contact with the first electrode.

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